



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



THYRISTOR/ DIODE and THYRISTOR/ THYRISTOR

ADD-A-pak™ GEN V Power Modules

Features

- High Voltage
- Industrial Standard Package
- Thick Al metal die and double stick bonding
- Thick copper baseplate
- UL E78996 approved
- 3500V_{RMS} isolating voltage

Benefits

- Up to 1600V
- Full compatible TO-240AA
- High Surge capability
- Easy Mounting on heatsink
- Al₂O₃ DBC insulator
- Heatsink grounded

27 A

Mechanical Description

The Generation V of Add-A-pak module combine the excellent thermal performance obtained by the usage of Direct Bonded Copper substrate with superior mechanical ruggedness, thanks to the insertion of a solid Copper baseplate at the bottom side of the device.

The Cu baseplate allow an easier mounting on the majority of heatsink with increased tolerance of surface roughness and improve thermal spread.

The Generation V of AAP module is manufactured without hard mold, eliminating in this way any possible direct stress on the leads.

The electrical terminals are secured against axial pull-out: they are fixed to the module housing via a click-stop feature already tested and proved as reliable on other IR modules.

Electrical Description

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

Major Ratings and Characteristics

| Parameters | IRK.26 | Units |
|--------------------------------------|-------------|-------------------|
| $I_{T(AV)}$ or $I_{F(AV)}$ @ 85°C | 27 | A |
| $I_{O(RMS)}$ (*) | 60 | A |
| I_{TSM} @ 50Hz | 400 | A |
| I_{FSM} @ 60Hz | 420 | A |
| I^2t @ 50Hz | 800 | A ² s |
| @ 60Hz | 730 | A ² s |
| $I^2\sqrt{t}$ | 8000 | A ² √s |
| V_{RRM} range | 400 to 1600 | V |
| T_{STG} | - 40 to 125 | °C |
| T_J | - 40 to 125 | °C |

(*) As AC switch.



IRK.26 Series

Bulletin I27130 rev. G 10/02

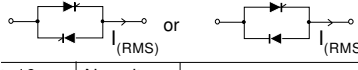
International
IRF Rectifier

ELECTRICAL SPECIFICATIONS

Voltage Ratings

| Type number | Voltage Code | V_{RRM} , maximum repetitive peak reverse voltage V | V_{RSM} , maximum non-repetitive peak reverse voltage V | V_{DRM} , max. repetitive peak off-state voltage, gate open circuit V | I_{RRM} I_{DRM} 125°C mA |
|-------------|--------------|--|--|--|---------------------------------------|
| IRK.26 | 04 | 400 | 500 | 400 | 15 |
| | 06 | 600 | 700 | 600 | |
| | 08 | 800 | 900 | 800 | |
| | 10 | 1000 | 1100 | 1000 | |
| | 12 | 1200 | 1300 | 1200 | |
| | 14 | 1400 | 1500 | 1400 | |
| | 16 | 1600 | 1700 | 1600 | |

On-state Conduction

| Parameters | IRK.26 | Units | Conditions | | | | | | | | | | | | | | |
|--|----------------------------|---|---|---|---|---------|-----------|--------|----------------|----------------------------|---------|-----------|--------|----------------------------|----------------------------|---------|----------------------|
| $I_{T(AV)}$ Max. average on-state current (Thyristors) | 27 | A | 180° conduction, half sine wave, $T_C = 85^\circ\text{C}$ | | | | | | | | | | | | | | |
| $I_{F(AV)}$ Max. average forward current (Diodes) | 27 | | | | | | | | | | | | | | | | |
| $I_{O(RMS)}$ Max. continuous RMS on-state current. As AC switch | 60 | | | | | | | | | | | | | | | | |
| I_{TSM} Max. peak, one cycle or non-repetitive on-state or forward current | 400 | | |  | | | | | | | | | | | | | |
| | 420 | | | | | | | | | | | | | | | | |
| | 335 | | | | | | | | | | | | | | | | |
| | 350 | | | | | | | | | | | | | | | | |
| | 470 | | | | | | | | | | | | | | | | |
| I_{FSM} | 490 | <table border="1"> <tr> <td>t=10ms</td> <td>No voltage</td> <td rowspan="2">Sinusoidal half wave, Initial $T_J = T_{Jmax}$.</td> </tr> <tr> <td>t=8.3ms</td> <td>reapplied</td> </tr> <tr> <td>t=10ms</td> <td>100% V_{RRM}</td> <td rowspan="2">Initial $T_J = T_{Jmax}$.</td> </tr> <tr> <td>t=8.3ms</td> <td>reapplied</td> </tr> <tr> <td>t=10ms</td> <td>$T_J = 25^\circ\text{C}$,</td> <td rowspan="2">Initial $T_J = T_{Jmax}$.</td> </tr> <tr> <td>t=8.3ms</td> <td>no voltage reapplied</td> </tr> </table> | t=10ms | No voltage | Sinusoidal half wave, Initial $T_J = T_{Jmax}$. | t=8.3ms | reapplied | t=10ms | 100% V_{RRM} | Initial $T_J = T_{Jmax}$. | t=8.3ms | reapplied | t=10ms | $T_J = 25^\circ\text{C}$, | Initial $T_J = T_{Jmax}$. | t=8.3ms | no voltage reapplied |
| | t=10ms | No voltage | Sinusoidal half wave, Initial $T_J = T_{Jmax}$. | | | | | | | | | | | | | | |
| t=8.3ms | reapplied | | | | | | | | | | | | | | | | |
| t=10ms | 100% V_{RRM} | Initial $T_J = T_{Jmax}$. | | | | | | | | | | | | | | | |
| t=8.3ms | reapplied | | | | | | | | | | | | | | | | |
| t=10ms | $T_J = 25^\circ\text{C}$, | Initial $T_J = T_{Jmax}$. | | | | | | | | | | | | | | | |
| t=8.3ms | no voltage reapplied | | | | | | | | | | | | | | | | |
| I^2t Max. I^2t for fusing | 800 | A ² s | t=10ms No voltage | | | | | | | | | | | | | | |
| | 730 | | t=8.3ms reapplied | | | | | | | | | | | | | | |
| | 560 | | t=10ms 100% V_{RRM} | | | | | | | | | | | | | | |
| | 510 | | t=8.3ms reapplied | | | | | | | | | | | | | | |
| | 1100 | | t=10ms $T_J = 25^\circ\text{C}$, | | | | | | | | | | | | | | |
| $I^2\sqrt{t}$ Max. $I^2\sqrt{t}$ for fusing (1) | 8000 | A ² √s | t=0.1 to 10ms, no voltage reappl. $T_J = T_{Jmax}$ | | | | | | | | | | | | | | |
| | | | t=8.3ms no voltage reapplied | | | | | | | | | | | | | | |
| $V_{T(TO)}$ Max. value of threshold voltage (2) | 0.92 | V | Low level (3) | | | | | | | | | | | | | | |
| | 0.95 | | High level (4) | | | | | | | | | | | | | | |
| r_t Max. value of on-state slope resistance (2) | 12.11 | mΩ | Low level (3) | | | | | | | | | | | | | | |
| | 11.82 | | High level (4) | | | | | | | | | | | | | | |
| V_{TM} Max. peak on-state or forward voltage | 1.95 | V | $I_{TM} = \pi \times I_{T(AV)}$ | | | | | | | | | | | | | | |
| | | | $I_{FM} = \pi \times I_{F(AV)}$ | | | | | | | | | | | | | | |
| di/dt Max. non-repetitive rate of rise of turned on current | 150 | A/μs | $T_J = 25^\circ\text{C}$, from 0.67 V_{DRM} , $I_{TM} = \pi \times I_{T(AV)}$, $I_g = 500\text{mA}$, $t_r < 0.5 \mu\text{s}$, $t_p > 6 \mu\text{s}$ | | | | | | | | | | | | | | |
| I_H Max. holding current | 200 | mA | $T_J = 25^\circ\text{C}$, anode supply = 6V, resistive load, gate open circuit | | | | | | | | | | | | | | |
| I_L Max. latching current | 400 | | $T_J = 25^\circ\text{C}$, anode supply = 6V, resistive load | | | | | | | | | | | | | | |

(1) I^2t for time $t_x = I^2\sqrt{t} \times \sqrt{t_x}$

(2) Average power = $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$

(3) $16.7\% \times \pi \times I_{AV} < I < \pi \times I_{AV}$

(4) $I > \pi \times I_{AV}$

Triggering

| Parameters | IRK.26 | Units | Conditions | |
|--|--------|---------------------------|--|---------------------------|
| P_{GM} Max. peak gate power | 10 | W | | |
| $P_{G(AV)}$ Max. average gate power | 2.5 | | | |
| I_{GM} Max. peak gate current | 2.5 | A | | |
| $-V_{GM}$ Max. peak negative gate voltage | 10 | V | Anode supply = 6V resistive load | |
| V_{GT} Max. gate voltage required to trigger | 4.0 | | | $T_J = -40^\circ\text{C}$ |
| | 2.5 | | | $T_J = 25^\circ\text{C}$ |
| | 1.7 | $T_J = 125^\circ\text{C}$ | | |
| I_{GT} Max. gate current required to trigger | 270 | mA | Anode supply = 6V resistive load | |
| | 150 | | | $T_J = 25^\circ\text{C}$ |
| | 80 | | | $T_J = 125^\circ\text{C}$ |
| V_{GD} Max. gate voltage that will not trigger | 0.25 | V | $T_J = 125^\circ\text{C}$, rated V_{DRM} applied | |
| I_{GD} Max. gate current that will not trigger | 6 | mA | $T_J = 125^\circ\text{C}$, rated V_{DRM} applied | |

Blocking

| Parameters | IRK.26 | Units | Conditions |
|--|------------------------------|------------------|--|
| I_{RRM} Max. peak reverse and off-state leakage current at V_{RRM} , V_{DRM} | 15 | mA | $T_J = 125^\circ\text{C}$, gate open circuit |
| V_{INS} RMS isolation voltage | 2500 (1 min) 3500 (1 sec) | V | 50 Hz, circuit to base, all terminals shorted |
| dv/dt Max. critical rate of rise | 500 | V/ μs | $T_J = 125^\circ\text{C}$, linear to $0.67 V_{DRM}$ |

(5) Available with dv/dt = 1000V/ μs , to complete code add S90 i.e. IRKT26/16AS90.

Thermal and Mechanical Specifications

| Parameters | IRK.26 | Units | Conditions |
|---|------------|---------|---|
| T_J Junction operating temperature range | -40 to 125 | °C | |
| T_{stg} Storage temp. range | -40 to 125 | | |
| R_{thJC} Max. internal thermal resistance, junction to case | 0.31 | K/W | Per module, DC operation |
| R_{thCS} Typical thermal resistance case to heatsink | 0.1 | | Mounting surface flat, smooth and greased |
| T Mounting torque $\pm 10\%$ to heatsink busbar | 5 | Nm | A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound |
| | 3 | | |
| wt Approximate weight | 110 (4) | gr (oz) | |
| Case style | TO-240AA | JEDEC | |

ΔR Conduction (per Junction)

(The following table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC)

| Devices | Sine half wave conduction | | | | | Rect. wave conduction | | | | | Units |
|---------|---------------------------|------|------|------|------|-----------------------|------|------|------|------|-------|
| | 180° | 120° | 90° | 60° | 30° | 180° | 120° | 90° | 60° | 30° | |
| IRK.26 | 0.23 | 0.27 | 0.34 | 0.48 | 0.73 | 0.17 | 0.28 | 0.36 | 0.49 | 0.73 | °C/W |

IRK.26 Series

Bulletin I27130 rev. G 10/02

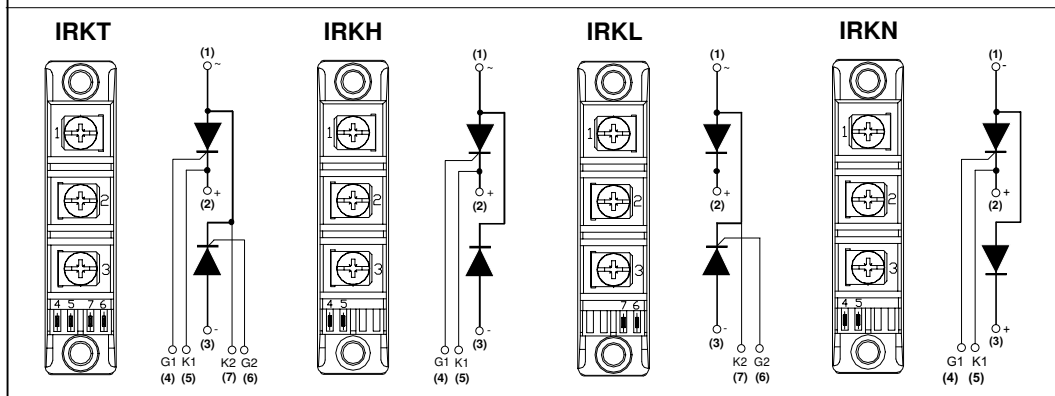
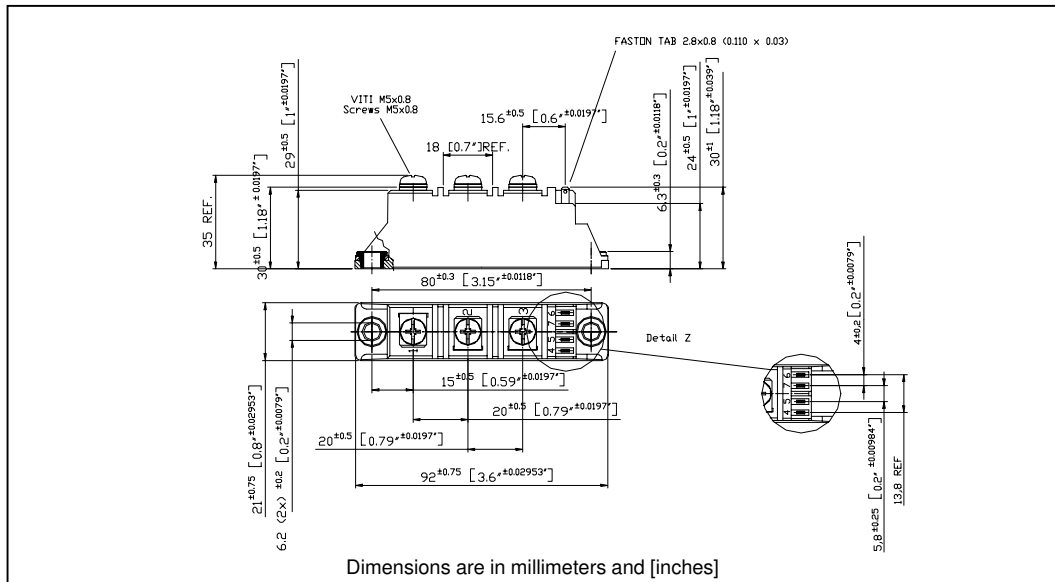
Ordering Information Table

| | | | | | | |
|--------------------|----------|-----------|----------|-----------|----------|------------|
| Device Code | | | | | | |
| IRK | T | 26 | / | 16 | A | S90 |
| ① | ② | ③ | | ④ | ⑤ | ⑥ |

| | |
|---|--|
| <p>1 - Module type</p> <p>2 - Circuit configuration (See Circuit Configuration table below)</p> <p>3 - Current code **</p> <p>4 - Voltage code (See Voltage Ratings table)</p> <p>5 - A : Gen V</p> <p>6 - dv/dt code: S90 = dv/dt 1000 V/μs No letter = dv/dt 500 V/μs</p> | <p>** Available with no auxiliary cathode. To specify change: 26 to 27</p> <p>e.g. : IRKT27/16A etc.</p> |
|---|--|

IRK.27 types
With no auxiliary cathode

Outline Table



NOTE: To order the Optional Hardware see Bulletin I27900

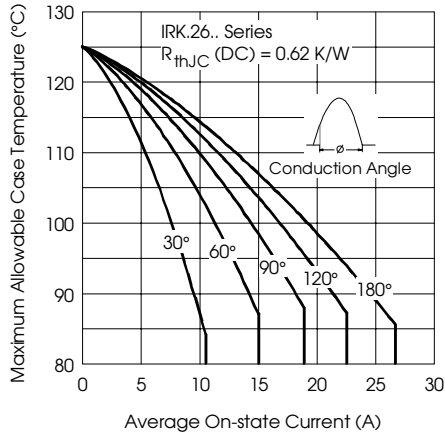


Fig. 1 - Current Ratings Characteristics

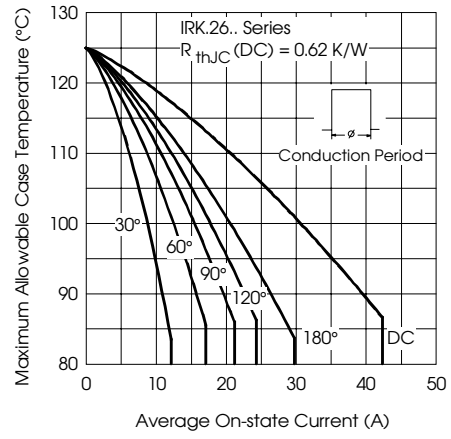


Fig. 2 - Current Ratings Characteristics

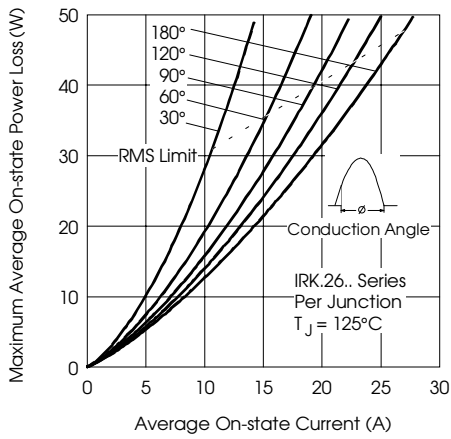


Fig. 3 - On-state Power Loss Characteristics

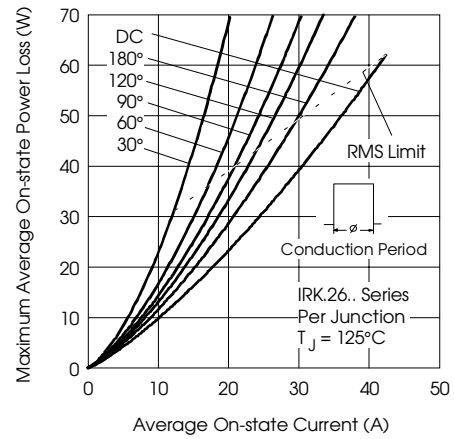


Fig. 4 - On-state Power Loss Characteristics

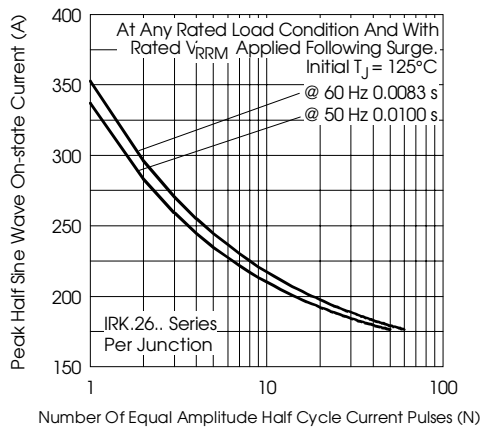


Fig. 5 - Maximum Non-Repetitive Surge Current

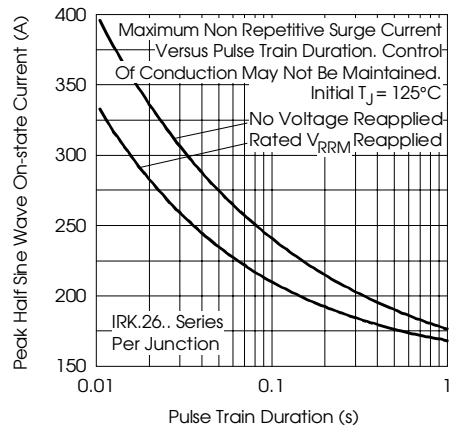


Fig. 6 - Maximum Non-Repetitive Surge Current

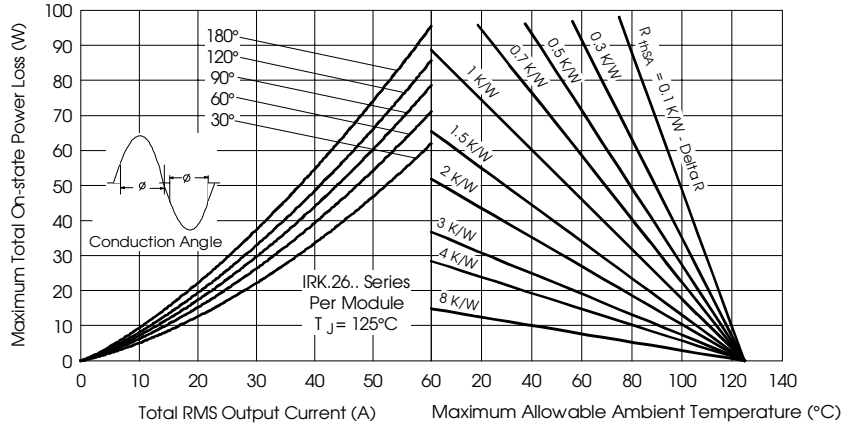


Fig. 7 - On-state Power Loss Characteristics

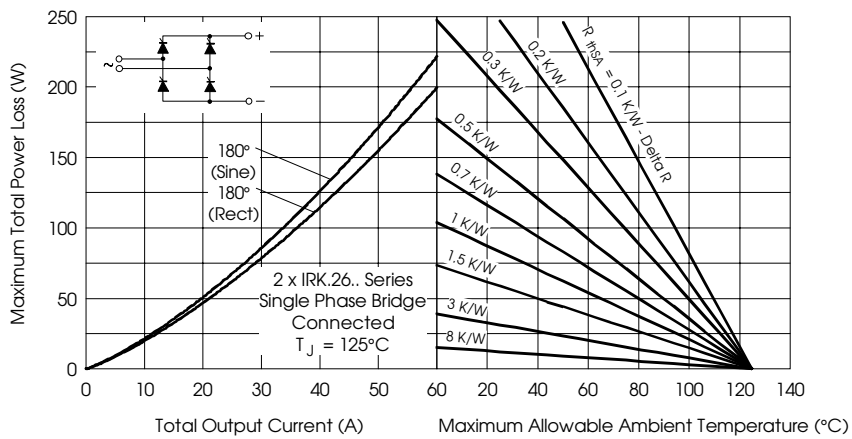


Fig. 8 - On-state Power Loss Characteristics

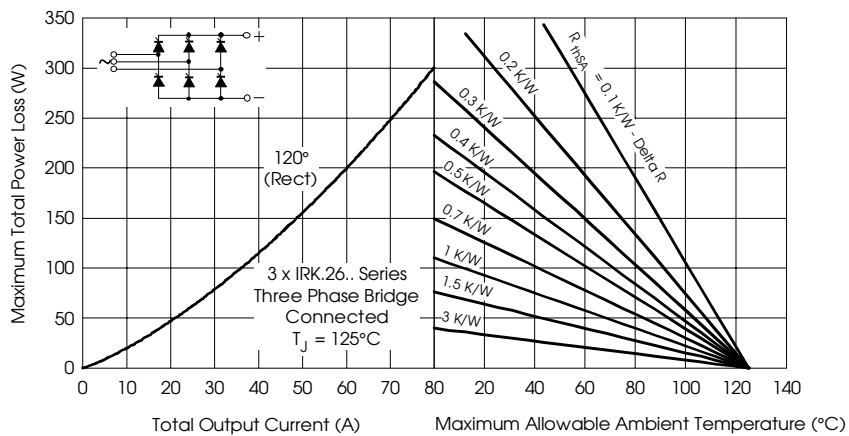


Fig. 9 - On-state Power Loss Characteristics

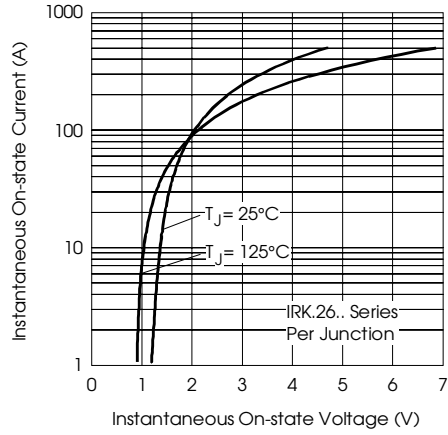


Fig. 10 - On-state Voltage Drop Characteristics

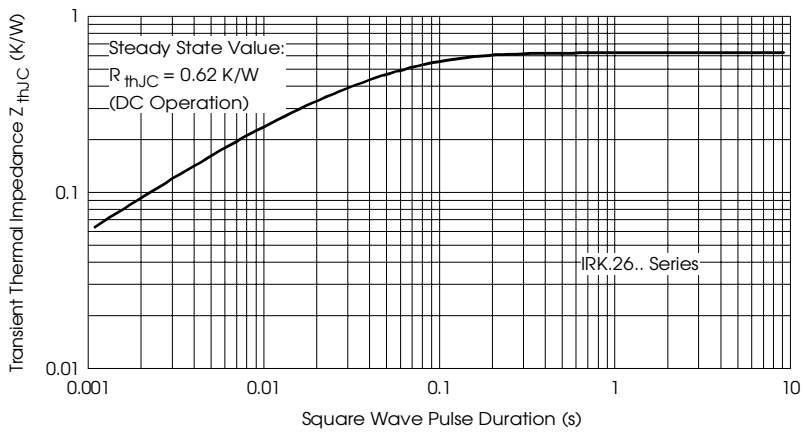


Fig. 11 - Thermal Impedance Z_{thJC} Characteristics

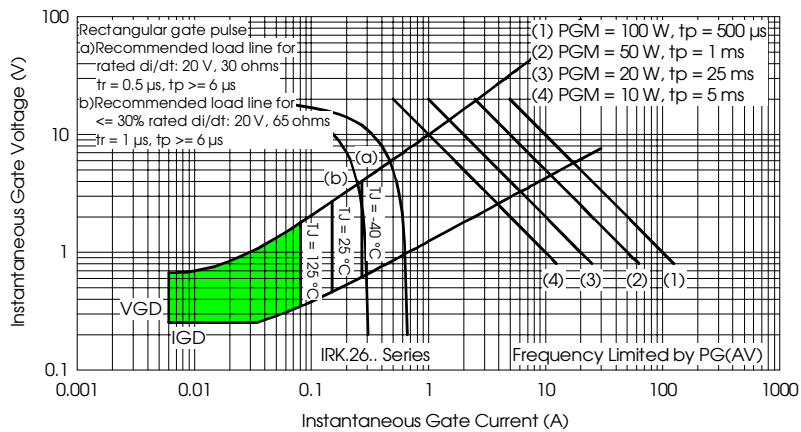


Fig. 12- Gate Characteristics

IRK.26 Series

Bulletin I27130 rev. G 10/02

International
IOR Rectifier

Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7309
Visit us at www.irf.com for sales contact information. 10/02